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1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	- -	- -	16 14	A	T_C=25 °C T_C=100 °C
Pulsed drain current[1]	$I_{D,pulse}$	-	-	64	A	T_C=25 °C
Avalanche energy, single pulse	E_{AS}	-	-	56	mJ	I_D=14.4 A, R_{GS}=25 Ω
Reverse diode peak dv/dt	dv/dt	-	-	60	kV/µs	I_D=36 A, V_{DS}=150 V, di/dt=1000 A/µs, $T_{j,max}$=175 °C
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	150	W	T_C=25 °C
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	-

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	0.6	1	K/W	-
Thermal resistance, junction - ambient, minimal footprint	R_{thJA}	-	-	75	K/W	-
Thermal resistance, junction - ambient, 6 cm^2 cooling area[2]	R_{thJA}	-	-	50	K/W	-

3 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	300	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	2	3	4	V	V_{DS}=V_{GS}, I_D=90 µA
Zero gate voltage drain current	I_{DSS}	- -	0.1 10	1 100	µA	V_{DS}=240 V, V_{GS}=0 V, T_j=25 °C V_{DS}=240 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	1	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	-	114	130	mΩ	V_{GS}=10 V, I_D=16 A
Gate resistance	R_G	-	3.3	5	Ω	-
Transconductance	g_{fs}	19	38	-	S	|V_{DS}|>2|I_D|$R_{DS(on)max}$, I_D=16 A

[1] See Diagram 3
[2] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	1840	2450	pF	V_{GS}=0 V, V_{DS}=150 V, f=1 MHz
Output capacitance[1)]	C_{oss}	-	76	102	pF	V_{GS}=0 V, V_{DS}=150 V, f=1 MHz
Reverse transfer capacitance[1)]	C_{rss}	-	5.4	-	pF	V_{GS}=0 V, V_{DS}=150 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	8.0	-	ns	V_{DD}=150 V, V_{GS}=10 V, I_D=8 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r	-	4.0	-	ns	V_{DD}=150 V, V_{GS}=10 V, I_D=8 A, $R_{G,ext}$=1.6 Ω
Turn-off delay time	$t_{d(off)}$	-	19	-	ns	V_{DD}=150 V, V_{GS}=10 V, I_D=8 A, $R_{G,ext}$=1.6 Ω
Fall time	t_f	-	4.0	-	ns	V_{DD}=150 V, V_{GS}=10 V, I_D=8 A, $R_{G,ext}$=1.6 Ω

Table 6 Gate charge characteristics[2)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	8.0	-	nC	V_{DD}=150 V, I_D=16 A, V_{GS}=0 to 10 V
Gate to drain charge	Q_{gd}	-	2.9	-	nC	V_{DD}=150 V, I_D=16 A, V_{GS}=0 to 10 V
Switching charge	Q_{sw}	-	5.4	-	nC	V_{DD}=150 V, I_D=16 A, V_{GS}=0 to 10 V
Gate charge total[1)]	Q_g	-	23	30	nC	V_{DD}=150 V, I_D=16 A, V_{GS}=0 to 10 V
Gate plateau voltage	$V_{plateau}$	-	4.4	-	V	V_{DD}=150 V, I_D=16 A, V_{GS}=0 to 10 V
Output charge	Q_{oss}	-	48	-	nC	V_{DD}=150 V, V_{GS}=0 V

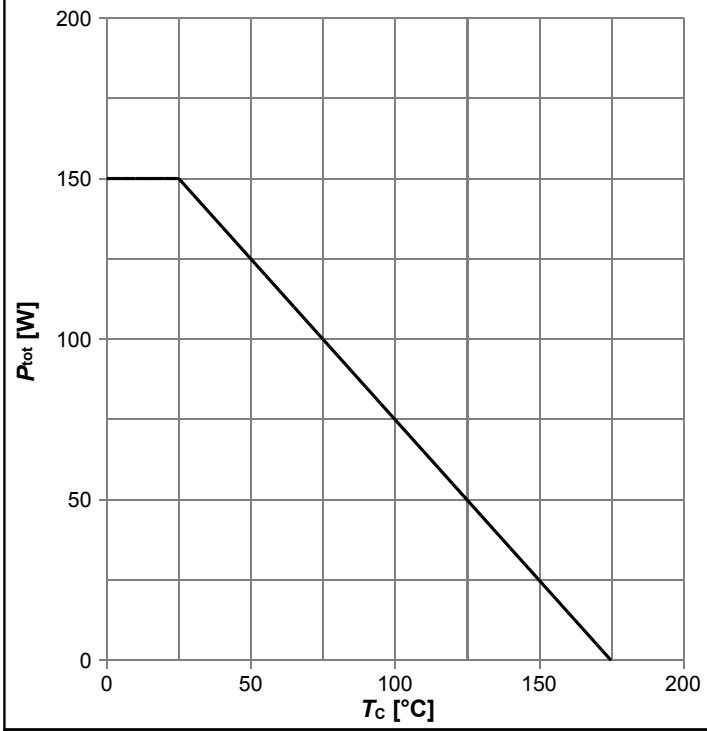
Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continous forward current	I_S	-	-	16	A	T_C=25 °C
Diode pulse current[3)]	$I_{S,pulse}$	-	-	64	A	T_C=25 °C
Diode hard commutation current[4)]	$I_{S,hard}$	-	-	16	A	T_C=25 °C, di_F/dt=1000 A/µs
Diode forward voltage	V_{SD}	-	0.9	1.2	V	V_{GS}=0 V, I_F=16 A, T_j=25 °C
Reverse recovery time[1)]	t_{rr}	-	111	222	ns	V_R=150 V, I_F=12.6A, di_F/dt=100 A/µs
Reverse recovery charge[1)]	Q_{rr}	-	249	498	nC	V_R=150 V, I_F=12.6A, di_F/dt=100 A/µs

[1)] Defined by design. Not subject to production test
[2)] See ″Gate charge waveforms″ for parameter definition
[3)] Diode pulse current is defined by thermal and/or package limits
[4)] Maximum allowed hard-commutated current through diode at di/dt=1000 A/µs

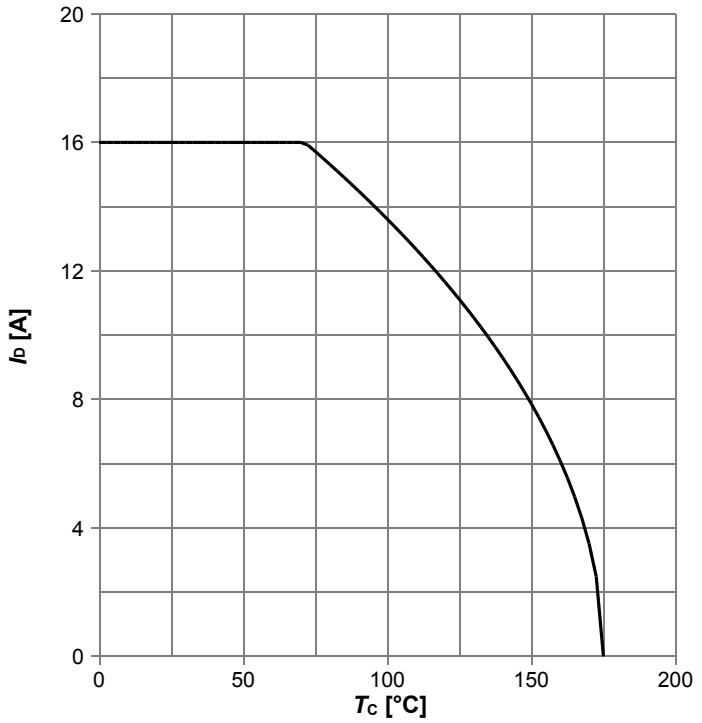
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



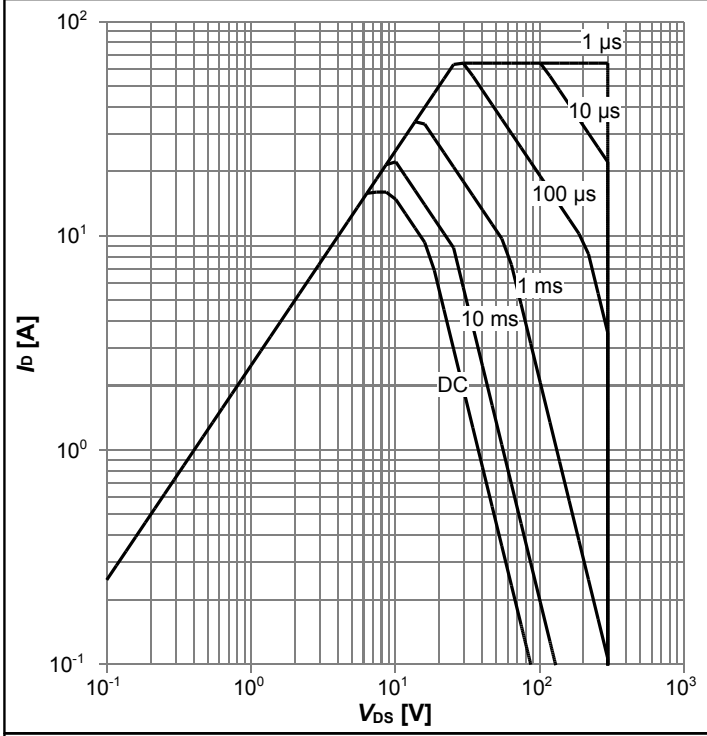
$P_{tot}=f(T_C)$

Diagram 2: Drain current



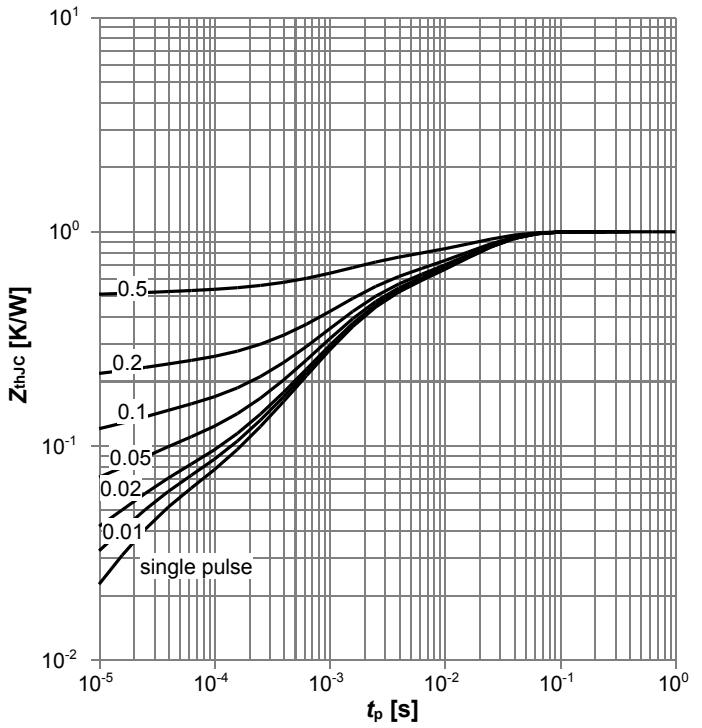
$I_D=f(T_C)$; $V_{GS}\geq 10$ V

Diagram 3: Safe operating area



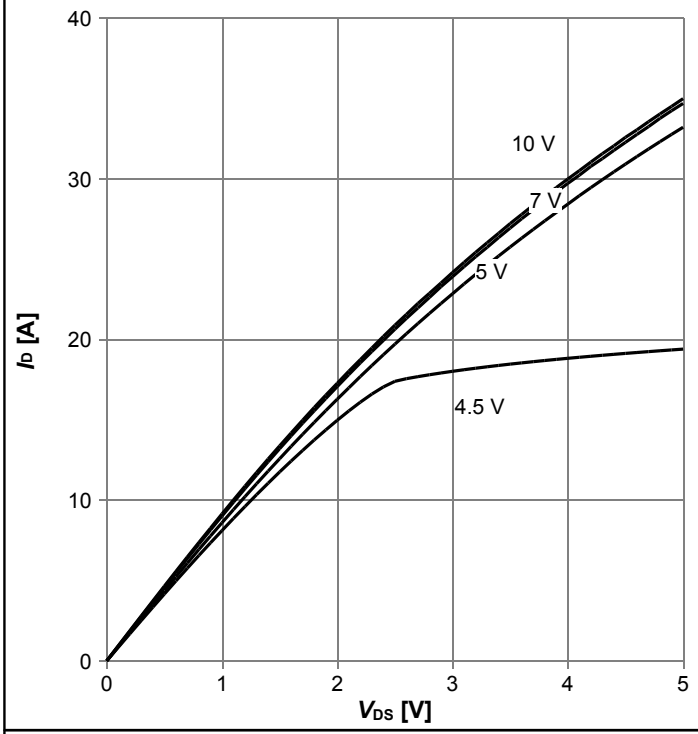
$I_D=f(V_{DS})$; T_C=25 °C; D=0; parameter: t_p

Diagram 4: Max. transient thermal impedance



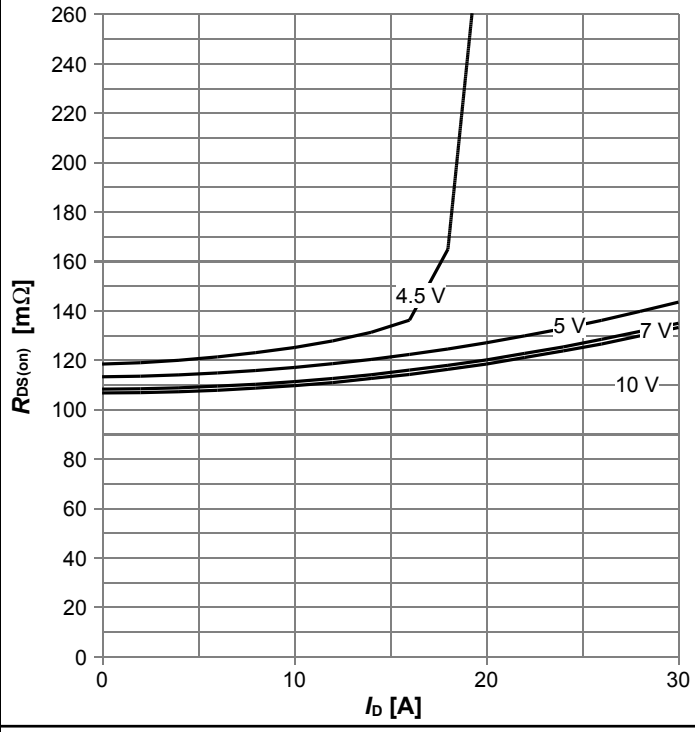
$Z_{thJC}=f(t_p)$; parameter: $D=t_p/T$

Diagram 5: Typ. output characteristics



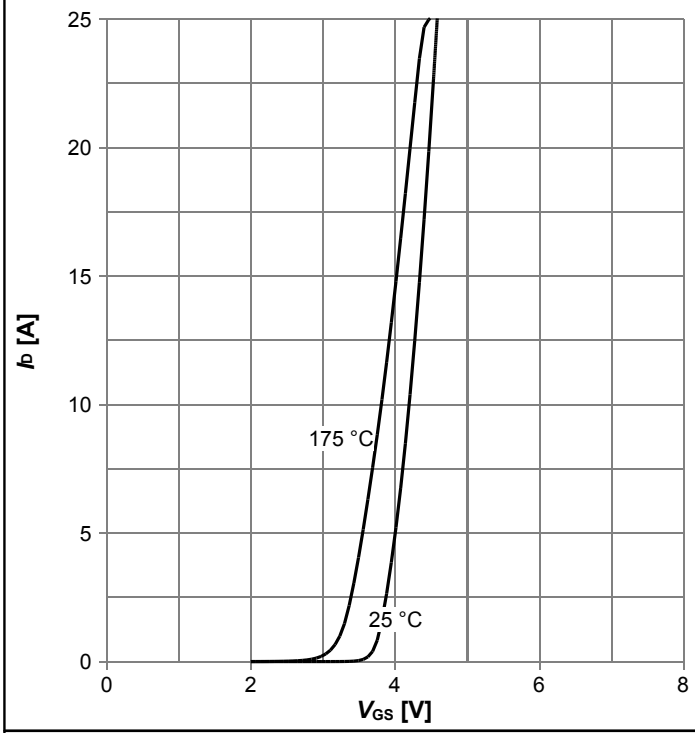
$I_D=f(V_{DS})$; $T_j=25$ °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



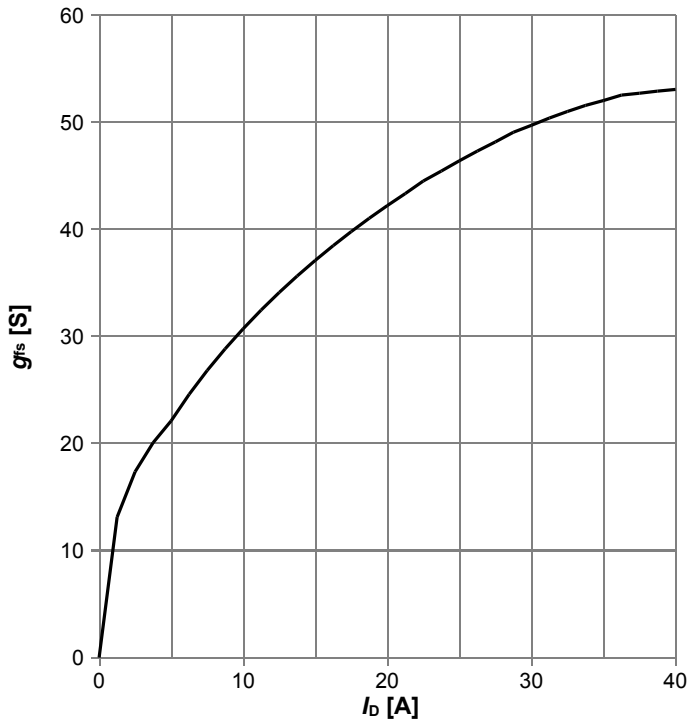
$R_{DS(on)}=f(I_D)$; $T_j=25$ °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



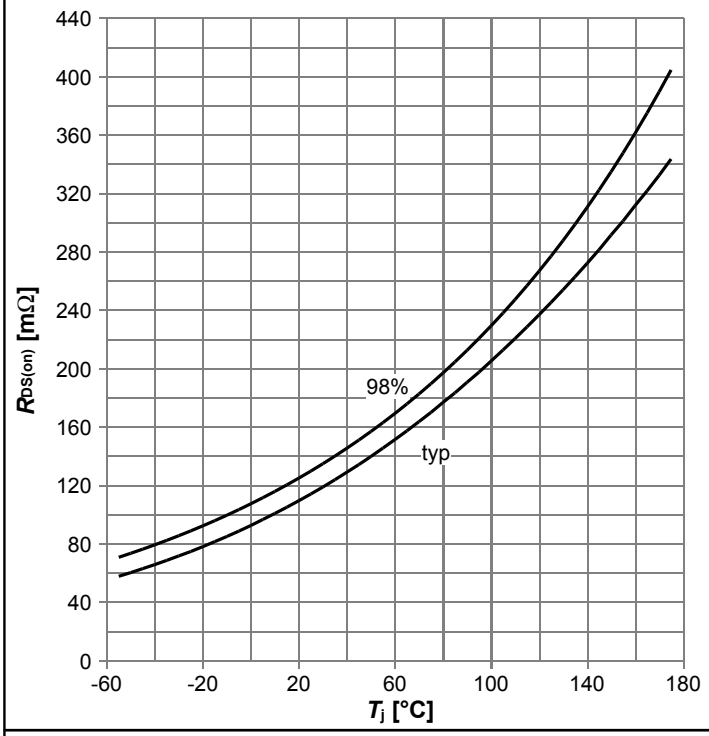
$I_D=f(V_{GS})$; $|V_{DS}|>2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. forward transconductance



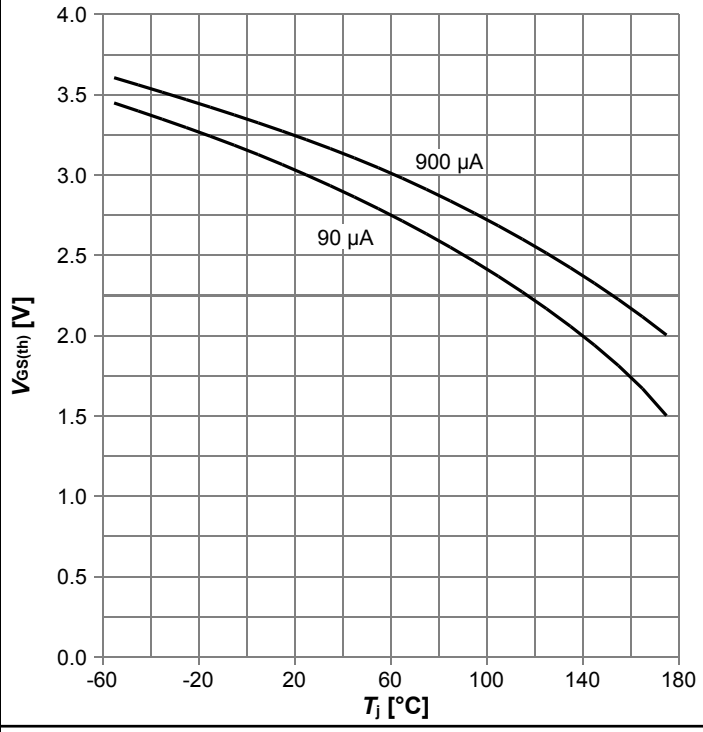
$g_{fs}=f(I_D)$; $T_j=25$ °C

Diagram 9: Drain-source on-state resistance



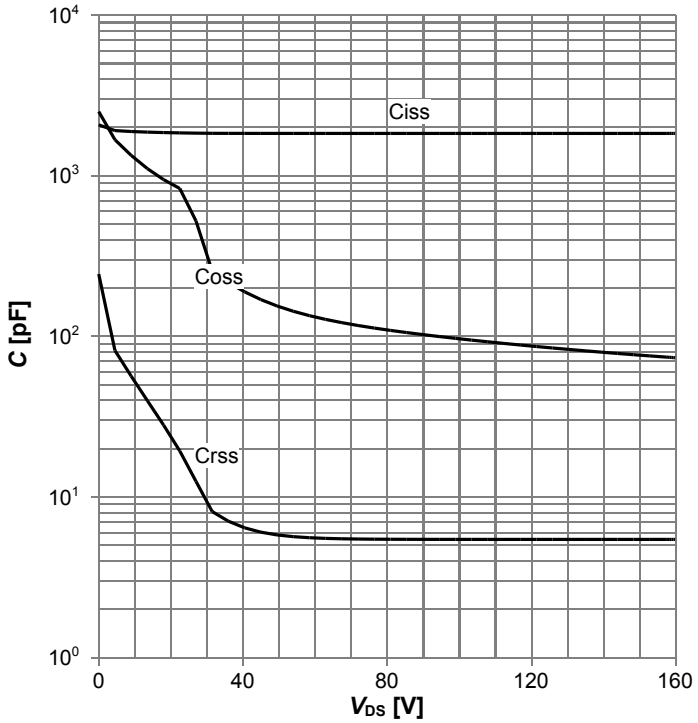
$R_{DS(on)}$=f(T_j); I_D=16 A; V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



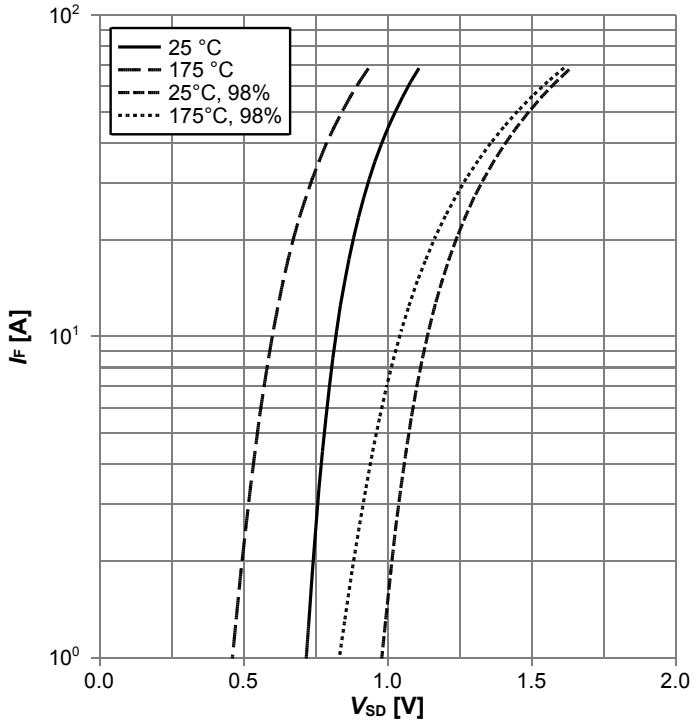
$V_{GS(th)}$=f(T_j); V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



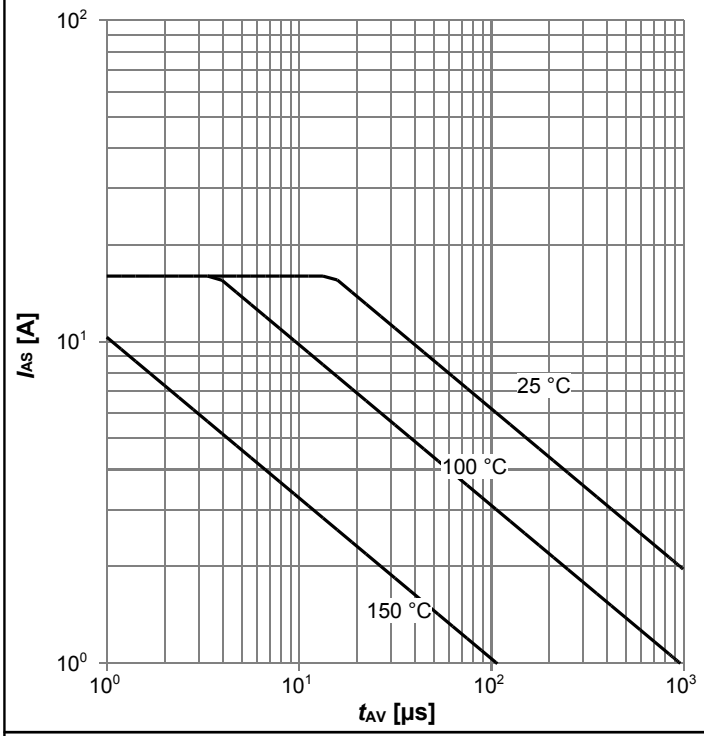
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



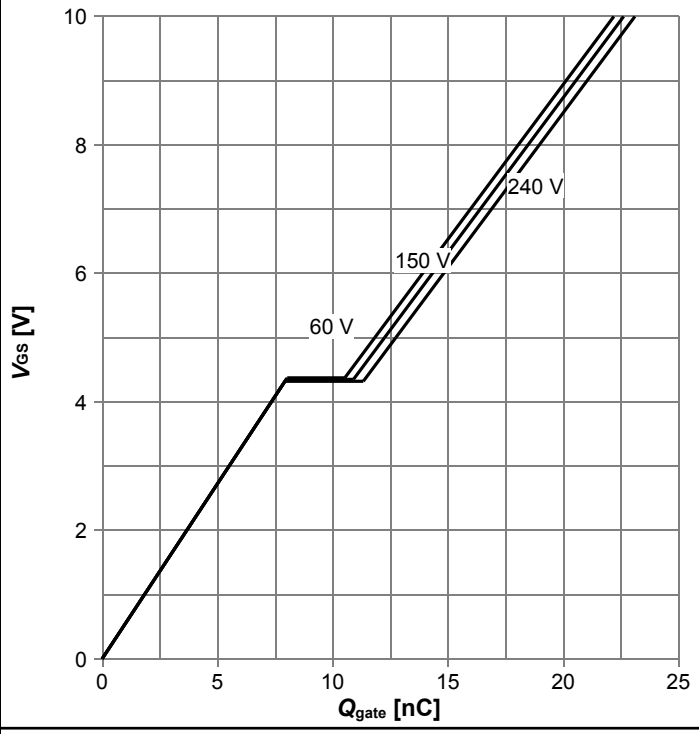
I_F=f(V_{SD}); parameter: T_j

Diagram 13: Avalanche characteristics



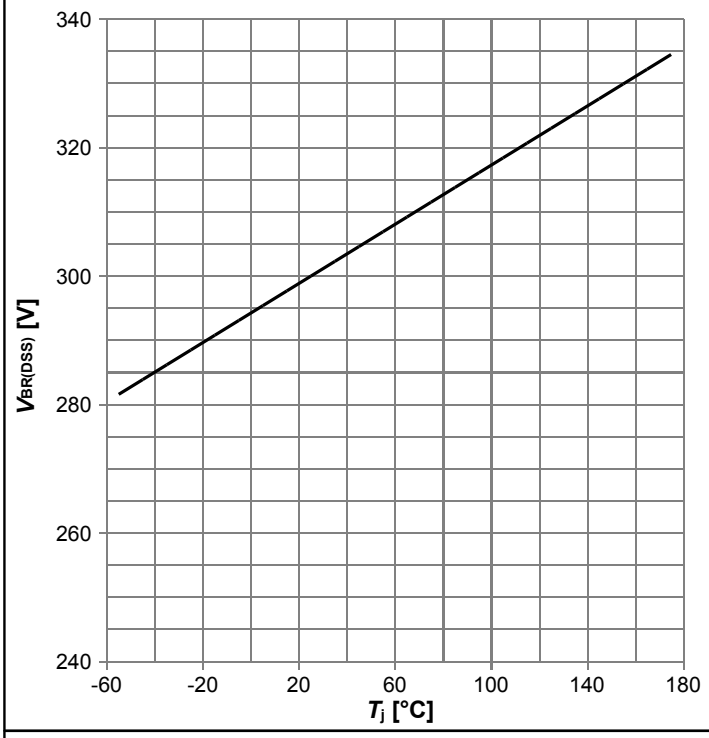
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



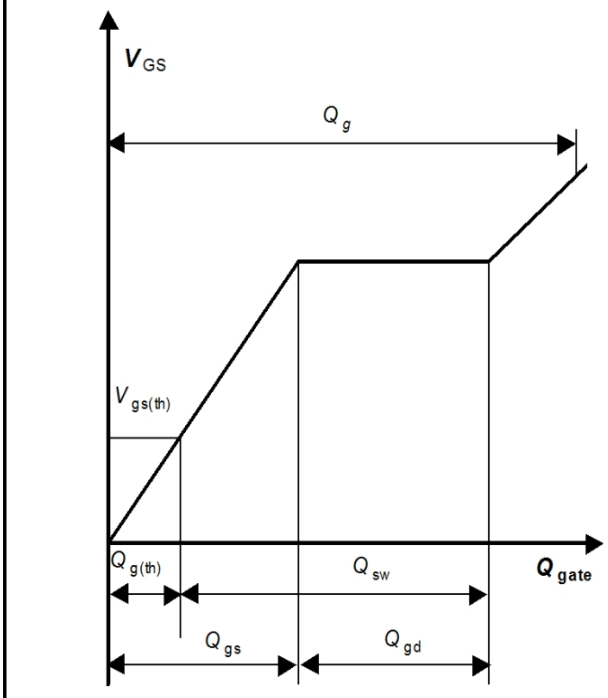
V_{GS}=f(Q_{gate}); I_D=16 A pulsed; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

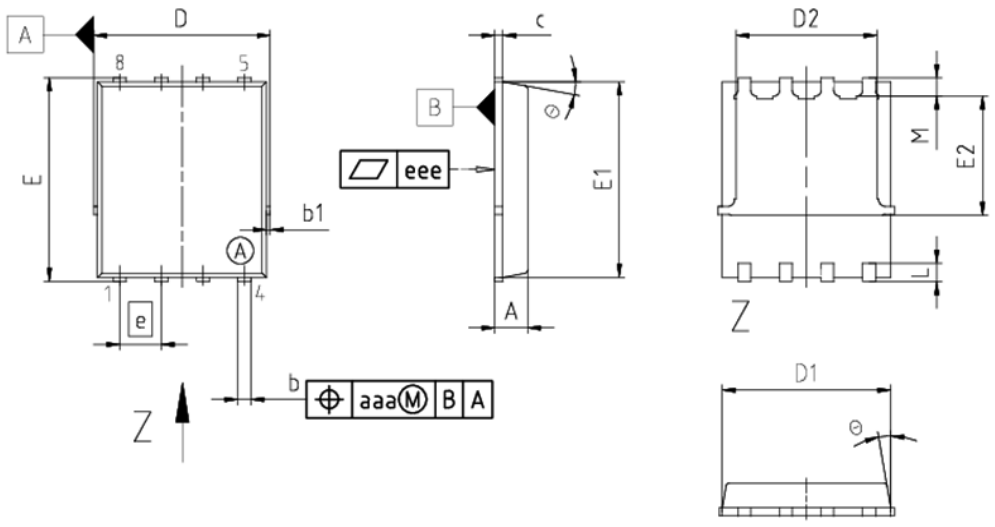


$V_{BR(DSS)}$=f(T_j); I_D=1 mA

Gate charge waveforms



5 Package Outlines



DIM	MILLIMETERS	
	MIN	MAX
A	0.90	1.10
b	0.31	0.54
b1	0.02	0.22
c	0.15	0.35
D	5.15	5.49
D1	4.95	5.35
D2	3.70	4.40
E	5.95	6.35
E1	5.70	6.10
E2	3.40	3.80
e	1.27	
N	8	
L	0.45	0.71
M	0.45	0.75
Θ	8.5°	12°
aaa	0.25	
eee	0.08	

DOCUMENT NO.
Z8B00003332

SCALE
0 2 0 2 4mm

EUROPEAN PROJECTION

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10-04-2013

REVISION
04

Figure 1 Outline PG-TDSON-8, dimensions in mm

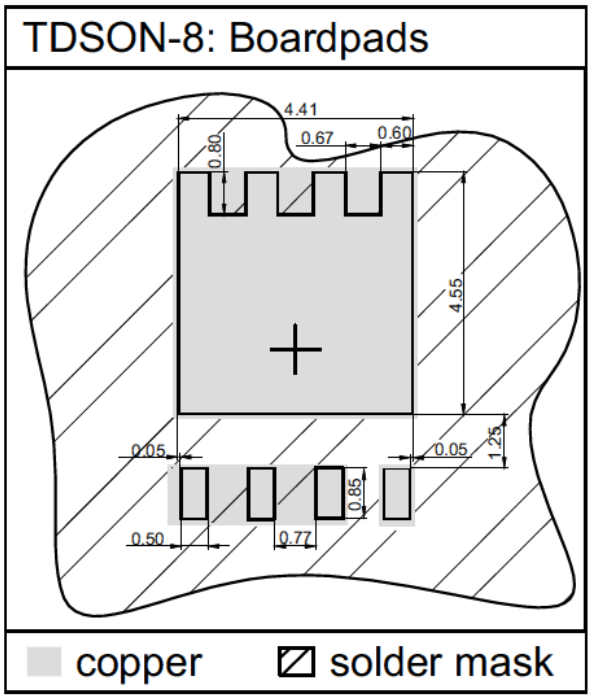

Figure 2 Outline Footprint (TDSON-8)

Revision History

BSC13DN30NSFD

Revision: 2016-12-05, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
1.2	2016-04-26	Release of Preliminary Datasheet
1.3	2016-05-13	Rev. 1.3 (preliminary datasheet)
2.0	2016-10-21	Release of final version
2.1	2016-12-05	Update Eas

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